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| Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary) | Atty Docket No. NOVLP089/ NVLS-2887 Applicant: Cho et al. Filing Date March 11, 2004 Application No.: 10/800,377 Group 2812 |
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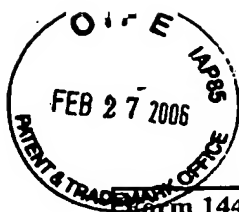
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| Examiner | <div style="text-align: center;"> </div> | |
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| Information Disclosure Statement By Applicant | Applicant: Cho et al. | |
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| Examiner | Date Considered | |
| W. J. C. Anderson | 3/11/06 | |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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| Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary) | Atty Docket No. | Application No.: |
| | NOVLP089/ NVLS-2887 | 10/800,377 |
| | Applicant: | |
| | Cho et al. | |
| | Filing Date | Group |
| | March 11, 2004 | 2812 |

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| 20 | C3 | Gangpadhyay et al., "The First International Surface Cleaning Workshop," Northeastern University, November 11-14, 2002 |
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| K. R. [Signature] | | 3/16/06 |

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



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| Form 1449 (Modified) | Atty Docket No. NOVLP089/ NVLS-2887 | Application No.: 10/800,377 |
| Information Disclosure Statement By Applicant | Applicant: Cho et al. | |
| (Use Several Sheets if Necessary) | Filing Date March 11, 2004 | Group 2812 |

U.S. Patent Documents

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| | A1 | | | | | | |
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Foreign Patent or Published Foreign Patent Application

| Examiner Initial | No. | Document No. | Publication Date | Country or Patent Office | Class | Sub- class | Translation | |
|---------------------|-----|-----------------|---------------------|-----------------------------|-------|---------------|-------------|----|
| | | | | | | | Yes | No |
| | B1 | | | | | | | |
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| <i>W</i> | C1 | Tipton et al., "Method For Removal Of Porogens From Porous Low-K Films Using Supercritical Fluids", U.S. Patent No. 10/672,305, filed Sept 26, 2003, Office Action dated September 1, 2005 (Atty Dkt: NOVLP069). |
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| Examiner <i>NPICARAT</i> | | Date Considered <i>3/16/06</i> |

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